



S9015

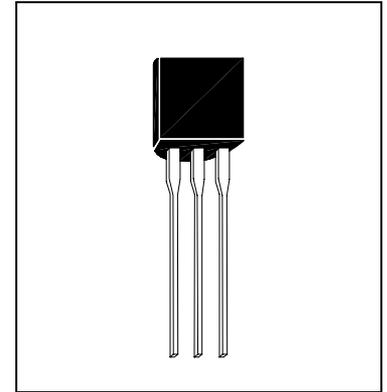
PNP EPITAXIAL PLANAR TRANSISTOR

Description

The S9015 is designed for use in pre-amplifier of low level and low noise.

Features

- High Total Power Dissipation. (PD:450mW)
- Complementary to S9014
- High hFE and Good Linearity.



Absolute Maximum Ratings

- Maximum Temperatures
Storage Temperature -55~+150°C
Junction Temperature +150°C Maximum
- Maximum Power Dissipation
Total Power Dissipation (Ta=25°C) 450 mW
- Maximum Voltages and Currents (Ta=25°C)
VCBO Collector to Base Voltage 50 V
VCEO Collector to Emitter Voltage 45 V
VEBO Emitter to Base Voltage 5 V
IC Collector Current 100 mA

Characteristics (Ta=25°C)

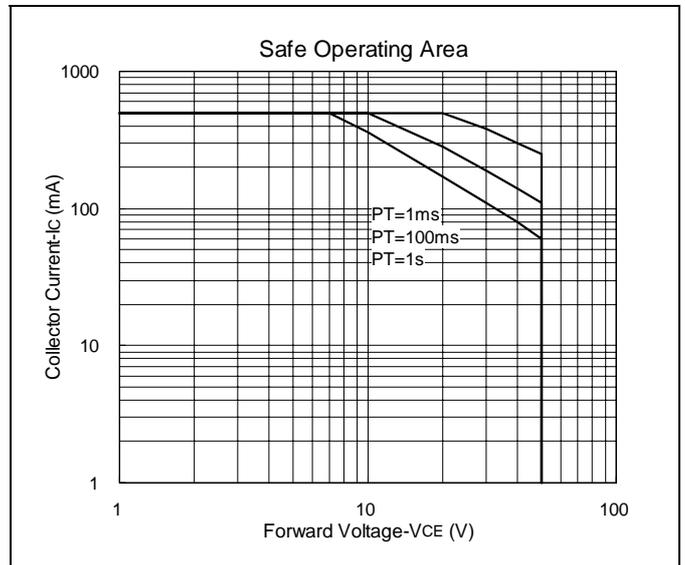
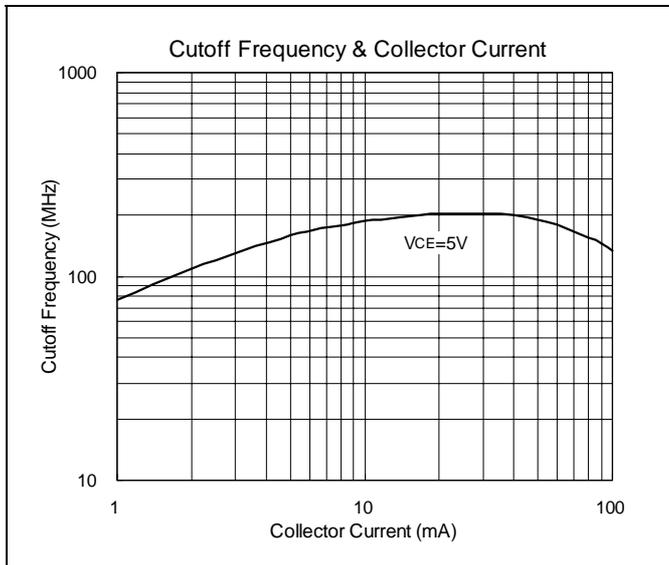
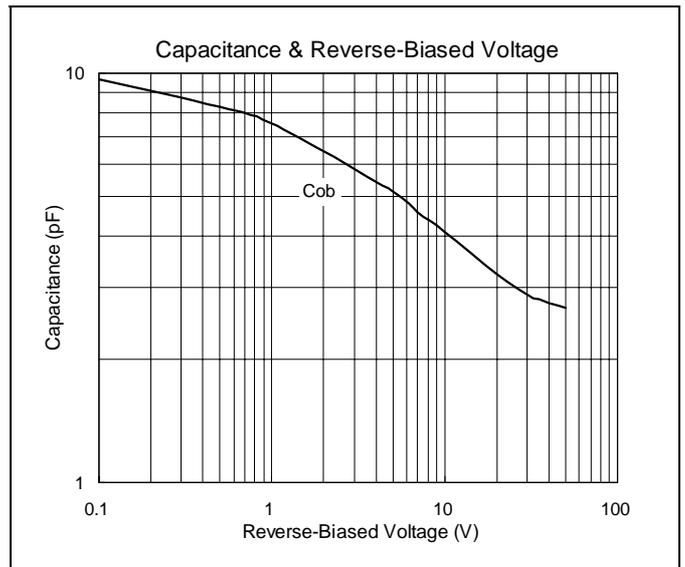
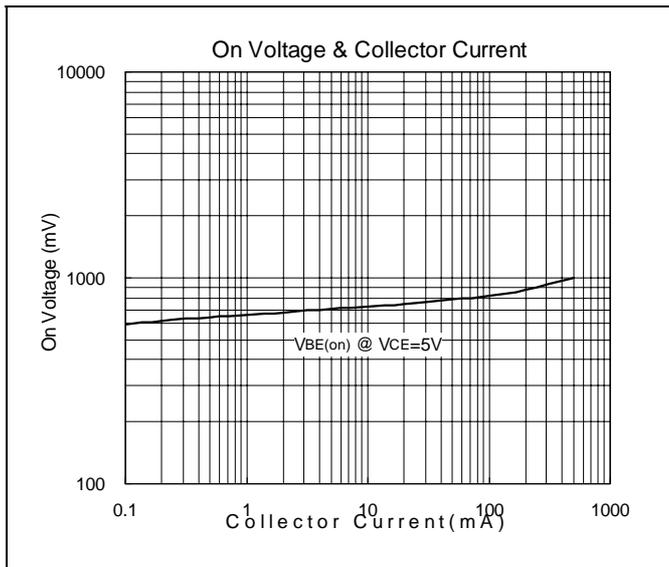
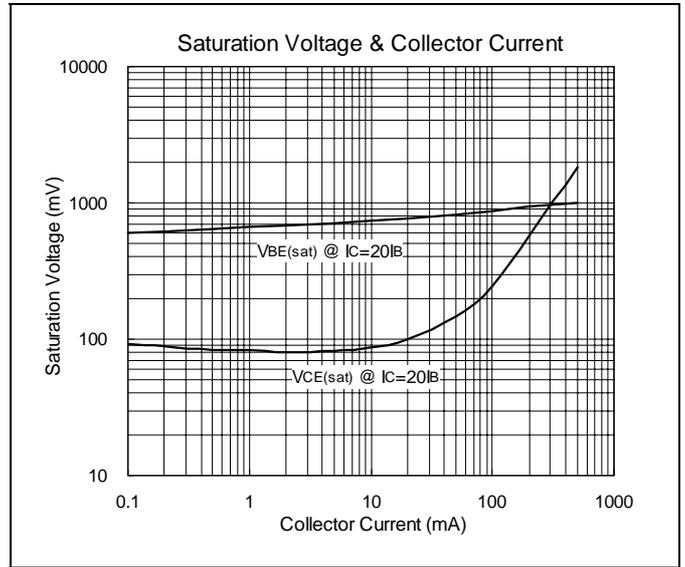
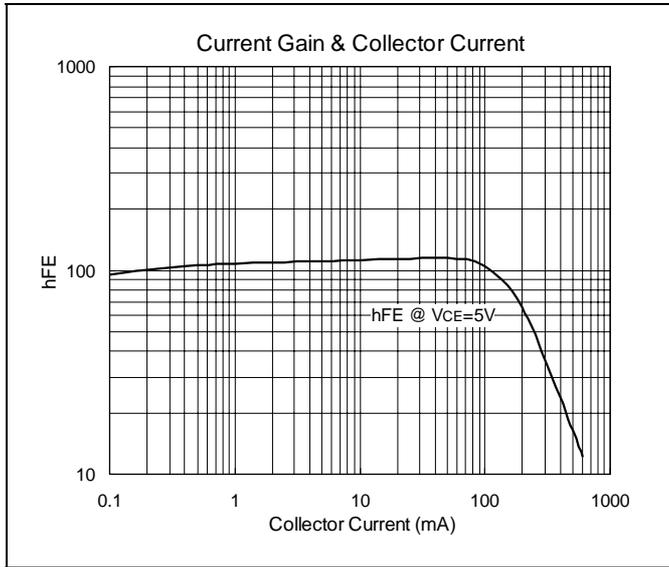
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	50	-	-	V	IC=100uA, IE=0
BVCEO	45	-	-	V	IC=1mA, IB=0
BVEBO	5.0	-	-	V	IE=100uA, IC=0
ICBO	-	-	50	nA	VCB=50V, IE=0
IEBO	-	-	50	nA	VEB=5V, IC=0
VCE(sat)	-	0.20	0.7	V	IC=100mA, IB=5mA
VBE(sat)	-	0.82	1.0	V	IC=100mA, IB=5mA
VBE(on)	0.6	0.65	0.75	V	VCE=5V, IC=2mA
hFE	100	200	600		VCE=5V, IC=1mA
Cob	-	4.5	7.0	pF	VCB=10V, f=1MHz, IE=0
fT	100	190	-	MHz	VCE=5V, IC=10mA

Classification on hFE1

Rank	B	C
Range	100-300	200-600

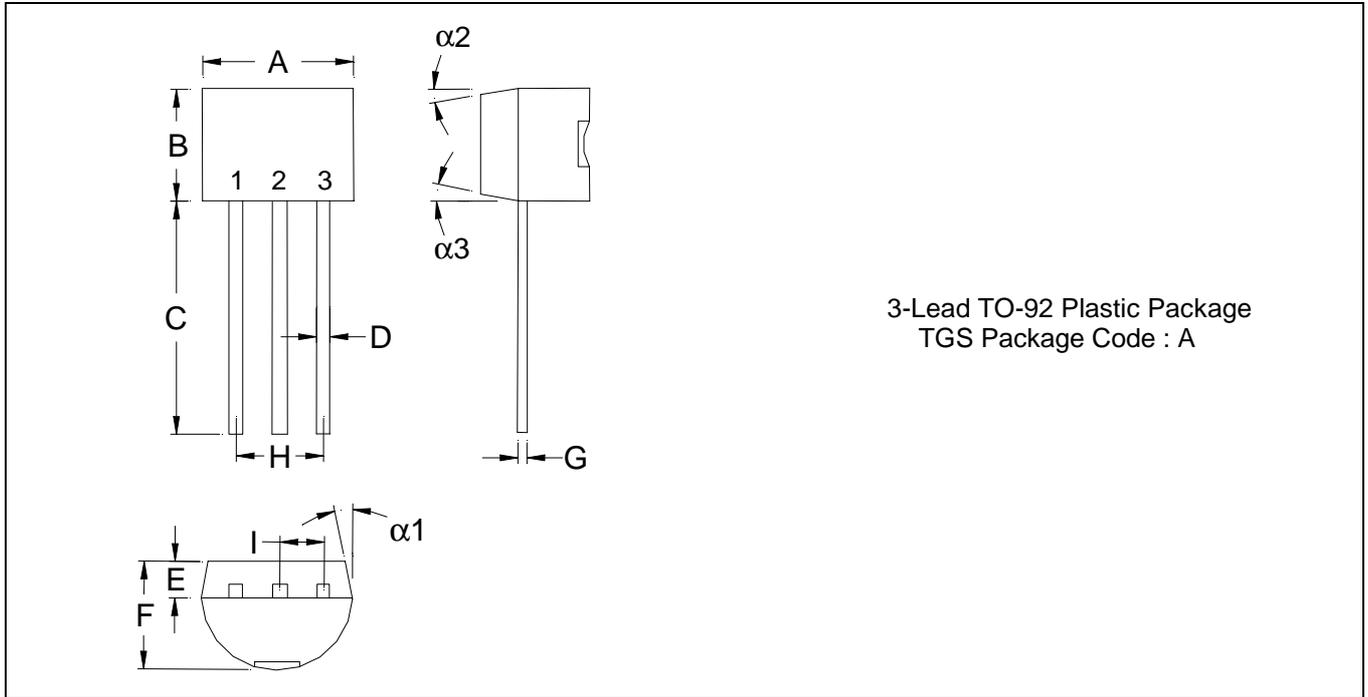


Characteristics Curve





TO-92 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°